



JCS3205H

主要参数 MAIN CHARACTERISTICS

I_D	110 A
V_{DS}	55 V
$R_{DS(on)}$ (@ $V_{GS}=10V$)	8 m Ω
Q_g -typ	78nC

用途

- 高频开关电源
- UPS 电源

APPLICATIONS

- High efficiency switch mode power supplies
- UPS

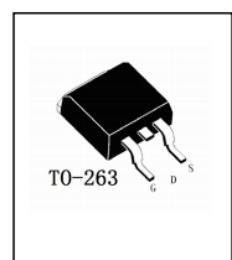
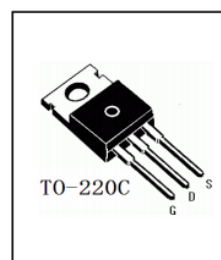
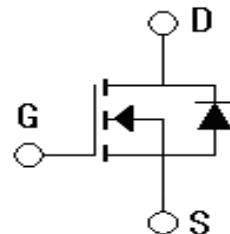
产品特性

- 低栅极电荷
- 低 C_{RSS} (典型值 197pF)
- 开关速度快
- 产品全部经过雪崩测试
- 高抗 dv/dt 能力
- RoHS 产品

FEATURES

- Low gate charge
- Low C_{RSS} (typical 197pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS product

封装 Package



订货信息 ORDER MESSAGE

订 货 型 号 Order codes				印 记 Marking	封 装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen-Free-Tube	有卤-编带 Halogen-Reel	无卤-编带 Halogen-Free-Reel		
JCS3205CH-C-B	JCS3205CH-C-BR	N/A	N/A	JCS3205CH	T0-220C
JCS3205SH-S-B	JCS3205SH-S-BR	JCS3205SH-S-A	JCS3205SH-S-AR	JCS3205SH	T0-263

绝对最大额定值 ABSOLUTE RATINGS ($T_c=25^{\circ}\text{C}$)

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit
最高漏极—源极直流电压 Drain-Source Voltage	V_{DSS}	55	V
连续漏极电流 Drain Current -continuous	I_{D} $T=25^{\circ}\text{C}$ $T=100^{\circ}\text{C}$	110*	A
		80*	A
最大脉冲漏极电流 (注 1) Drain Current – pulse (note 1)	I_{DM}	440*	A
最高栅源电压 Gate-Source Voltage	V_{GSS}	± 20	V
单脉冲雪崩能量 (注 2) Single Pulsed Avalanche Energy (note 2)	E_{AS}	2970	mJ
雪崩电流 (注 1) Avalanche Current (note 1)	I_{AR}	60	A
重复雪崩能量 (注 1) Repetitive Avalanche Current (note 1)	E_{AR}	20	mJ
二极管反向恢复最大电压变化速率 (注 3) Peak Diode Recovery dv/dt (note 3)	dv/dt	5.0	V/ns
耗散功率 Power Dissipation	P_{D} $T_c=25^{\circ}\text{C}$ -Derate above 25°C	200	W
		1.33	W/ $^{\circ}\text{C}$
最高结温及存储温度 Operating and Storage Temperature Range	$T_{\text{J}}, T_{\text{STG}}$	$-55 \sim +175$	$^{\circ}\text{C}$
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T_{L}	300	$^{\circ}\text{C}$

*漏极电流由最高结温限制

*Drain current limited by maximum junction temperature





电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
关态特性 Off –Characteristics						
漏—源击穿电压 Drain-Source Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	55	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D=250\mu A$, referenced to $25^\circ C$	-	0.057	-	V/ $^\circ C$
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=55V, V_{GS}=0V, T_C=25^\circ C$	-	-	1	μA
		$V_{DS}=44V, T_C=125^\circ C$	-	-	10	μA
正向栅极体漏电流 Gate-body leakage current, forward	I_{GSSF}	$V_{DS}=0V, V_{GS}=20V$	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	I_{GSSR}	$V_{DS}=0V, V_{GS}=-20V$	-	-	-100	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=250\mu A$	2.0	-	4.0	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$ $T=25^\circ C$	$V_{GS}=10V, I_D=60A$	-	7	8	m Ω
	$R_{DS(ON)}$ $T=100^\circ C$	$V_{GS}=10V, I_D=60A$	-	10.5	12	m Ω
正向跨导 Forward Transconductance	g_{fs}	$V_{DS}=28V, I_D=60A$ (note 4)	-	43	-	S
动态特性 Dynamic Characteristics						
栅电阻 Gate Resistance	R_g	$f=1.0MHz$, V_{DS} OPEN	0.5	1.8	2.6	Ω
输入电容 Input capacitance	C_{iss}	$V_{DS}=25V$, $V_{GS}=0V$, $f=1.0MHz$	1375	2750	5625	pF
输出电容 Output capacitance	C_{oss}		375	749	1124	pF
反向传输电容 Reverse transfer capacitance	C_{rss}		99	197	296	pF





电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics						
延迟时间 Turn-On delay time	$t_d(\text{on})$	$V_{DD}=28V, I_D=60A, R_G=25\Omega$ $V_{GS}=10V$ (note 4, 5)	-	17	26	ns
上升时间 Turn-On rise time	t_r		-	122	183	ns
延迟时间 Turn-Off delay time	$t_d(\text{off})$		-	57	86	ns
下降时间 Turn-Off Fall time	t_f		-	72	108	ns
栅极电荷总量 Total Gate Charge	Q_g	$V_{DS}=44V$,	38	78	117	nC
栅-源电荷 Gate-Source charge	Q_{gs}	$I_D=60A$	6.6	13.2	20	nC
栅-漏电荷 Gate-Drain charge	Q_{gd}	$V_{GS}=10V$ (note 4, 5)	18.9	37.8	56	nC
漏-源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings						
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current	I_S		-	-	110	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}		-	-	440	A
正向压降 Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$, $I_S=60A$	-		1.3	V
反向恢复时间 Reverse recovery time	t_{rr}	$V_{GS}=0V$, $I_S=60A$	-	67	127	ns
反向恢复电荷 Reverse recovery charge	Q_{rr}	$di_F/dt=100A/\mu s$ (note 4)	-	163	253	nC

热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	最大 Max	单 位 Unit
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	0.75	$^{\circ}C/W$
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	62.5	$^{\circ}C/W$

注释:

- 1: 脉冲宽度由最高结温限制
- 2: $L=0.5mH, I_{AS}=60A, V_{DD}=50V, R_G=25\Omega$, 起始结温 $T_J=25^{\circ}C$
- 3: $I_{SD} \leq 60A, di/dt \leq 300A/\mu s, V_{DD} \leq BV_{DSS}$, 起始结温 $T_J=25^{\circ}C$
- 4: 脉冲测试: 脉冲宽度 $\leq 300\mu s$, 占空比 $\leq 2\%$
- 5: 基本与工作温度无关

Notes:

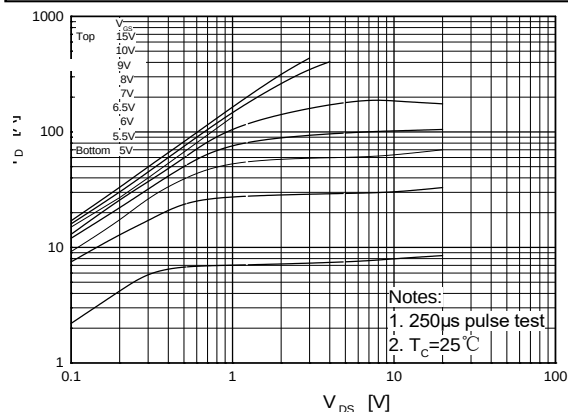
- 1: Pulse width limited by maximum junction temperature
- 2: $L=0.5mH, I_{AS}=60A, V_{DD}=50V, R_G=25\Omega$, Starting $T_J=25^{\circ}C$
- 3: $I_{SD} \leq 60A, di/dt \leq 300A/\mu s, V_{DD} \leq BV_{DSS}$, Starting $T_J=25^{\circ}C$
- 4: Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
- 5: Essentially independent of operating temperature



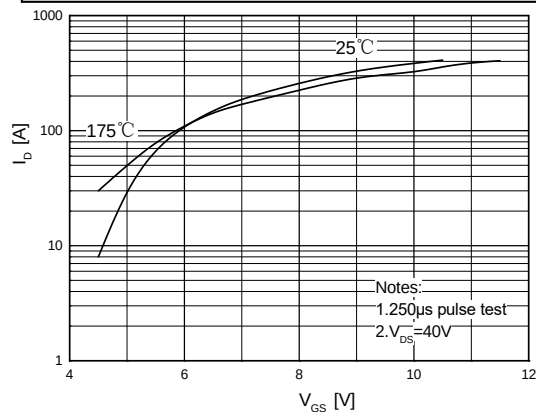


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

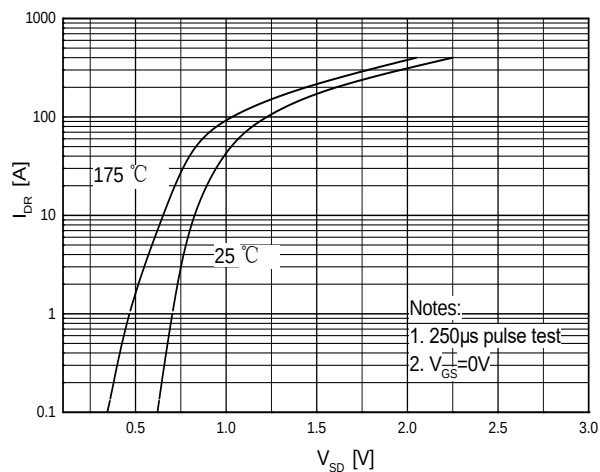
On-Region Characteristics



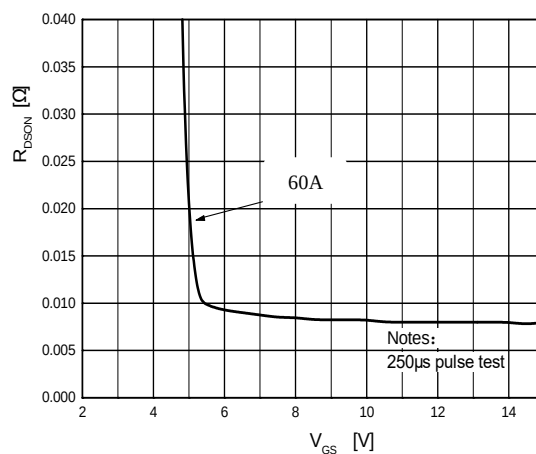
Transfer Characteristics



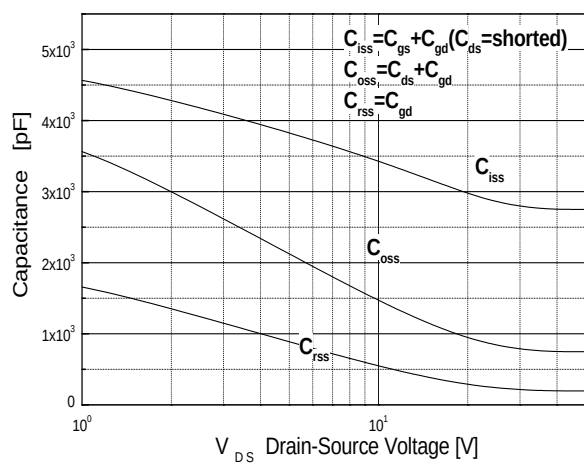
Body Diode Forward Voltage Variation vs. Source Current and Temperature



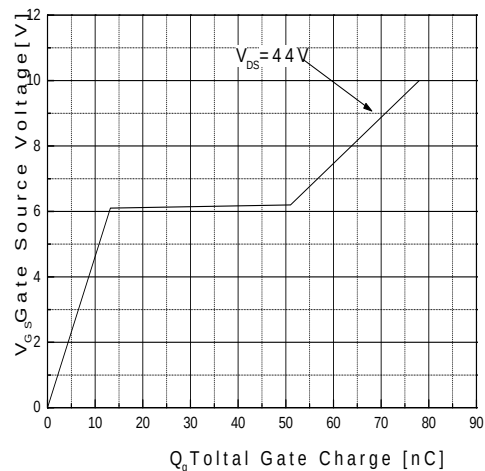
On-Resistance Variation vs. Drain Current and Gate Voltage



Capacitance Characteristics

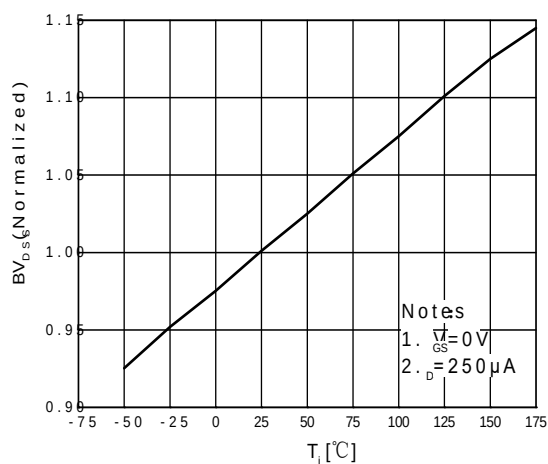
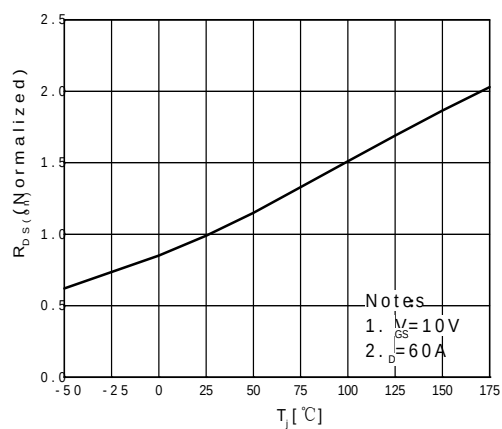
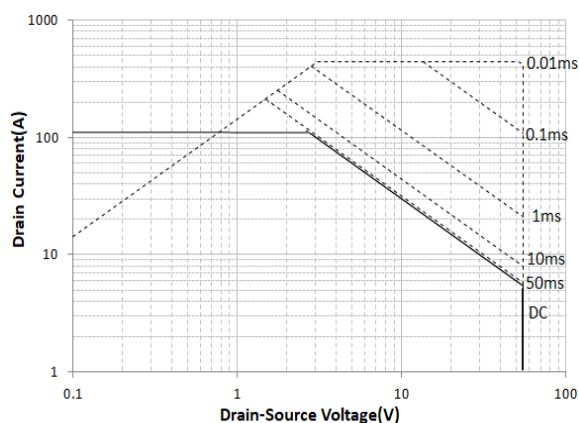
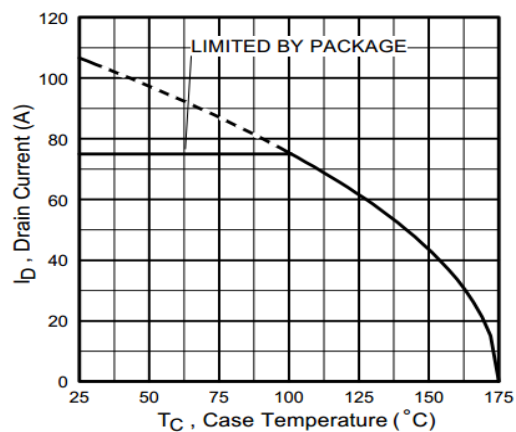
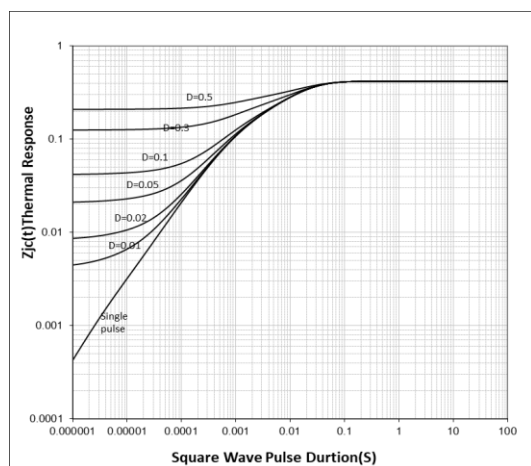
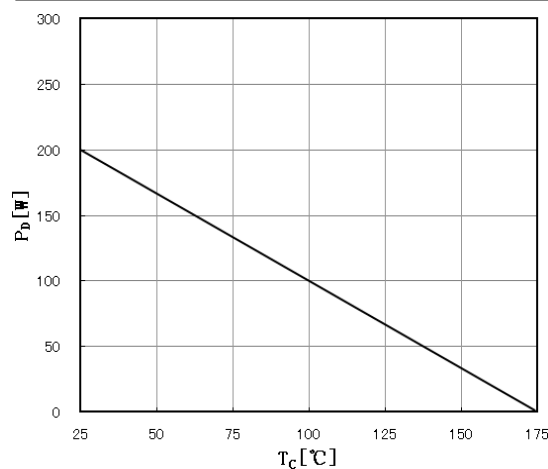


Gate Charge Characteristics





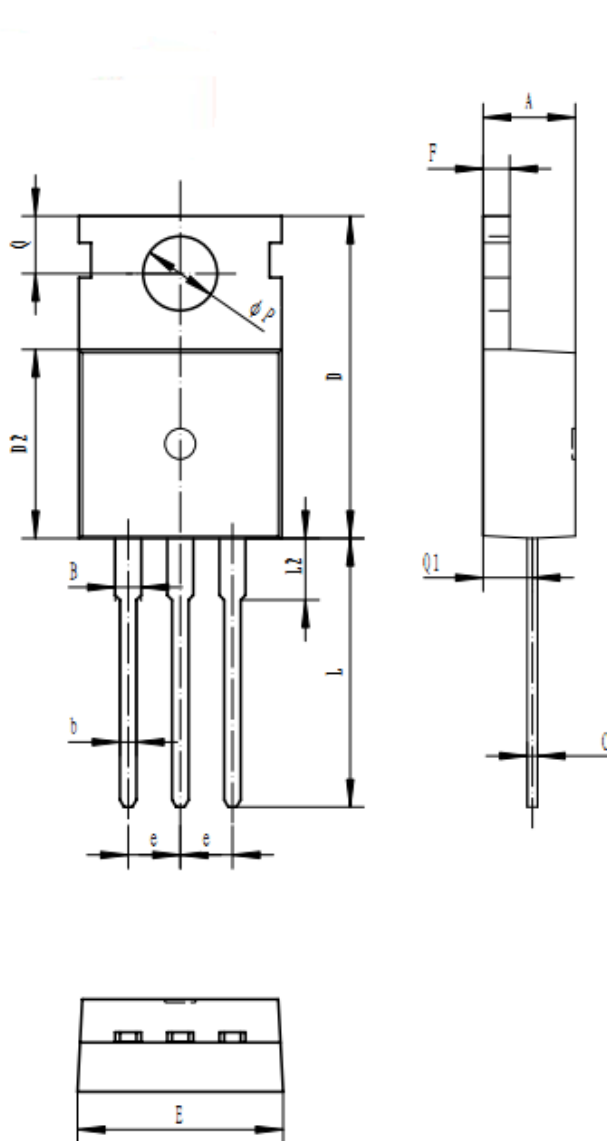
特征曲线 ELECTRICAL CHARACTERISTICS (curves)

Breakdown Voltage Variation
vs. TemperatureOn-Resistance Variation
vs. TemperatureMaximum Safe Operating Area
For JCS3205HMaximum Drain Current
vs. Case TemperatureTransient Thermal Response Curve
For JCS3205HPower Dissipation vs. Case
Temperature



TO-220C

单位 Unit: mm

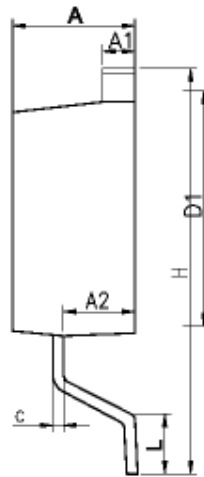
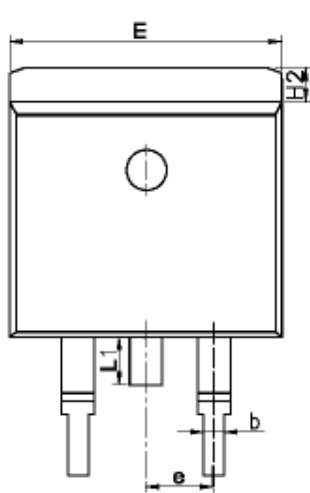


符号 symbol	MIN	MAX
A	4.30	4.70
B	1.22	1.40
b	0.70	0.95
c	0.40	0.65
D	15.20	16.20
D2	9.00	9.40
E	9.70	10.10
e	2.39	2.69
F	1.25	1.40
L	12.60	13.60
L2	2.80	3.20
Q	2.60	3.00
Q1	2.20	2.60
P	3.50	3.80



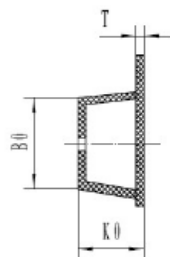
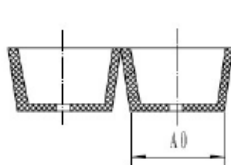
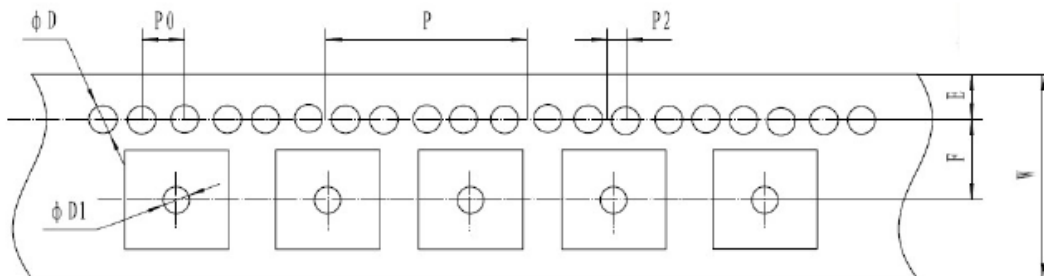
TO-263

单位 Unit: mm



SYMBOL	MM	
	MIN	MAX
A	4.30	4.80
A1	1.12	1.42
A2	2.54	2.84
b	0.67	1.00
c	0.29	0.52
D1	8.40	9.00
E	9.80	10.46
e	2.54BSC	
H	14.00	16.00
H2	1.12	1.45
L	1.50	3.10
L1	1.45	1.70

编带 REEL



产品尺寸规格 (UNIT: mm)					
规格	W	A0	E	F	D
尺寸	24 ± 0.3	10.9 ± 0.1	1.75 ± 0.1	11.5 ± 0.1	1.5 + 0.1/-0
规格	D1	P0	P2	P	T
尺寸	1.5 + 0.1/-0	4 ± 0.1	2 ± 0.1	16 ± 0.1	0.35 ± 0.05
规格	K0	B0			
尺寸	4.9 ± 0.1	16.0 ± 0.1			



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3. Please do not exceed the absolute maximum ratings of the device when circuit designing.
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